

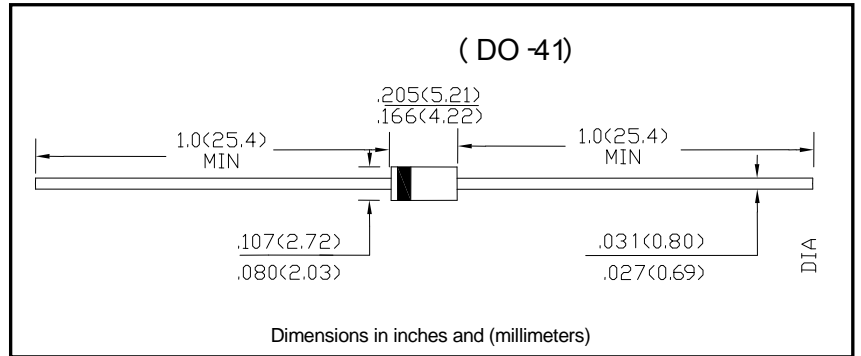
■特征 Features

- I_o 1A
- V_{RRM} 600V
- 玻璃钝化芯片 Glass passivated chip
- 耐正向浪涌电流能力高
High surge forward current capability

■用途 Applications

- 快速整流用

■外形尺寸和印记 Outline Dimensions and Mark



■极限值（绝对最大额定值）

Limiting Values（Absolute Maximum Rating）

参数名称 Item	符号 Symbol	单位 Unit	测试条件 Conditions	MUR160
反向重复峰值电压 Repetitive Peak Reverse Voltage	V_{RRM}	V		600
平均整流输出电流 Average Rectified Output Current	I_o	A	正弦半波 60Hz, 电阻负载, T_c (Fig.1) 60HZ Half-sine wave, Resistance load, T_c (Fig.1)	1
正向（不重复）浪涌电流 Surge(Non-repetitive)Forward Current	I_{FSM}	A	60HZ 正弦波, 一个周期, $T_a=25^\circ\text{C}$ 60HZ sine wave, 1 cycle, $T_a=25^\circ\text{C}$	30
贮存温度 Storage Temperature	T_{stg}	$^\circ\text{C}$		-55 ~ +175
结温 Junction Temperature	T_j	$^\circ\text{C}$		-55 ~ +150

■电特性（ $T_a=25^\circ\text{C}$ 除非另有规定）

Electrical Characteristics（ $T_a=25^\circ\text{C}$ Unless otherwise specified）

参数名称 Item	符号 Symbol	单位 Unit	测试条件 Conditions	MUR160	
正向峰值电压 Peak Forward Voltage	V_{FM}	V	@ $T_a=25^\circ\text{C}$ $I_F=1A$	1.30	
反向峰值电流 Peak Reverse Current	I_{RRM}	μA	$V_{RM}=V_{RRM}$	$T_a=25^\circ\text{C}$	5
				$T_a=150^\circ\text{C}$	300
反向恢复时间 Reverse Recovery Time	T_{rr}	ns	$I_F=0.5A$ $I_{RM}=1A$ $I_{RR}=0.25A$	50	
热阻 Thermal Resistance	$R_{\theta J-L}$	$^\circ\text{C/W}$	结和引线之间 Between junction and Line	24	

■ 特性曲线（典型） Characteristics(Typical)

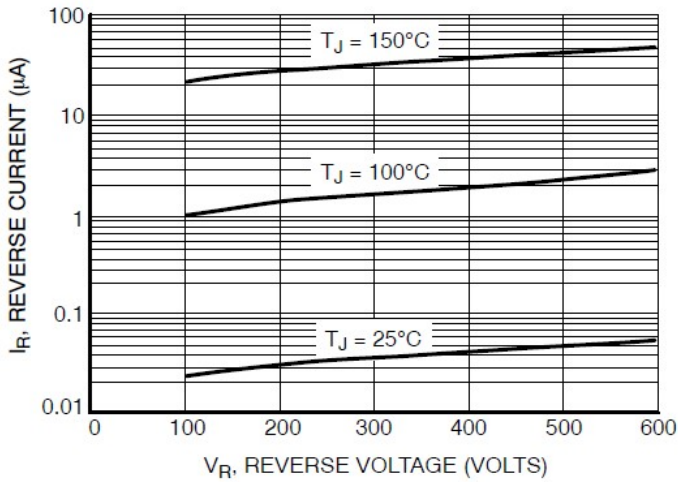


Figure 1. Typical Reverse Current

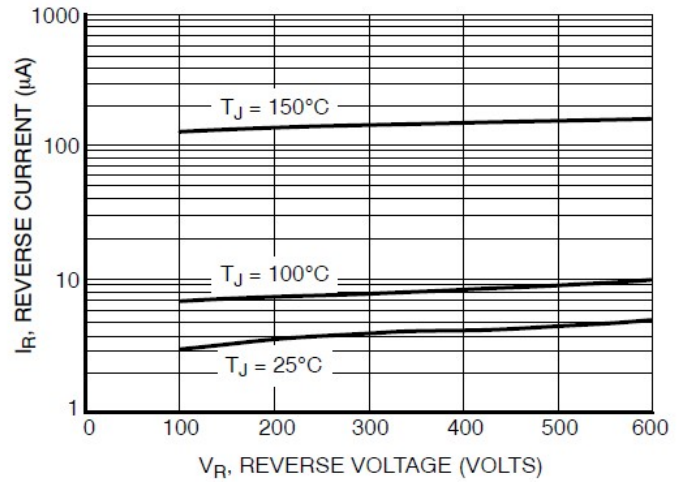


Figure 2. Maximum Reverse Current

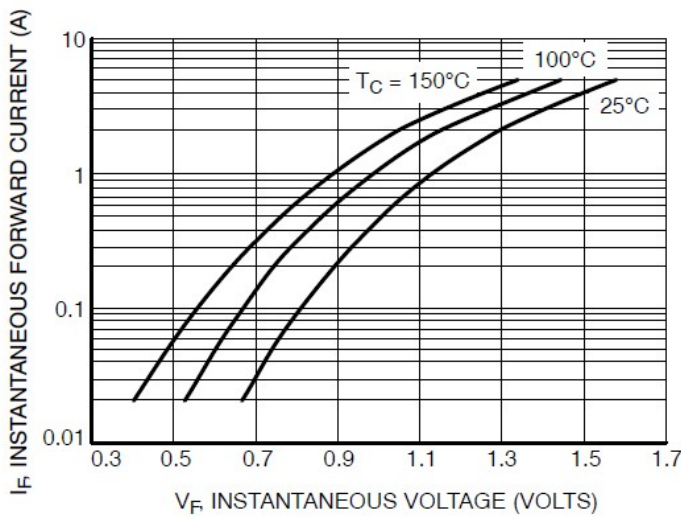


Figure 3. Typical Forward Voltage

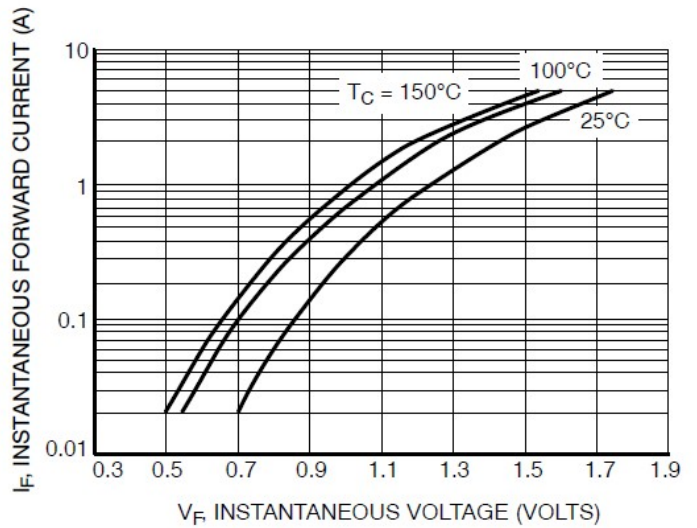


Figure 4. Maximum Forward Voltage

图5：反向恢复时间试验电路及测试波形示意图
Diagram of circuit and Testing wave form of reverse recovery time

